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A COLLECTION OF HYMNS OF THE CHRISTIAN APOSTOLIC CHURCH (YORUBA VERSION). These are extracted hymns from the printed ones, serving as a proof copy, you can also download the first 20 ...

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Download the C.A.C (Christian Apostolic Church) Hymn Book. Download the Christ Apostolic Church Yoruba Hymn Book Today. . is a Western African Christian denomination, the C.A.C church was founded in 1930 in.(i) Field of the Invention The present invention relates to semiconductor integrated circuits, and particularly to those to which a SOI (Silicon-on-Insulator) structure is applied. (ii) Description of the Prior Art In semiconductor integrated circuits or a semiconductor device having a SOI structure, the semiconductor active regions are formed on a buried oxide film or a buried silicon film. The semiconductor active regions are usually formed by implanting ions of impurity elements into a silicon semiconductor substrate and drive-in, annealing, and patterning processes are applied to the semiconductor substrate to form insulating gate isolating regions, buried silicon regions, source/drain regions of the n-channel MOS transistors and the p-channel MOS transistors and the like. In the case that the semiconductor substrate is a silicon semiconductor substrate which is the same kind as in the semiconductor substrate forming the semiconductor active regions, thermal stresses are produced at interfaces between the oxide film and the substrate and an active region and between the buried silicon regions and the silicon semiconductor substrate in the heat treatment for, e.g., oxygen (O.sub.2) ion implanting process, due to characteristics of the SOI structure and further there occurs a problem that cracks or peeling is produced at boundaries of the silicon semiconductor substrate and the buried silicon region, and that a leak current increases or the like due to defects caused by the cracks. A technique to prevent the problems has been proposed in Japanese Laid-Open patent application No. Hei 3-74751. In this technique, a semiconductor substrate is formed with a silicon oxide film thereon, oxygen ions are implanted into the silicon semiconductor substrate, thereafter a buried oxide film is formed on the silicon semiconductor substrate, an amorphous silicon semiconductor layer is formed on the buried oxide film, and the amorphous silicon semiconductor layer is crystallized. Thus, the semiconductor substrate is divided into the silicon active regions and the silicon-

oxide-buried-silicon active regions, whereby the thermal stresses caused between the silicon active regions and the silicon oxide film and between the silicon-oxide-buried-silicon regions c6a93da74d

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